

# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### ABSOLUTE MAXIMUM RATINGS

V <sub>CC</sub> to GND .....	-0.3V to +5.5V	Operating Case Temperature Range (Note 2) .....	-40°C to +100°C
LO1, LO2 to GND .....	±0.3V	Junction Temperature .....	+150°C
Any Other Pins to GND .....	-0.3V to (V <sub>CC</sub> + 0.3V)	Storage Temperature Range .....	-65°C to +150°C
RFMAIN, RFDIV, and LO_ Input Power .....	+20dBm	Lead Temperature (soldering, 10s) .....	+300°C
RFMAIN, RFDIV Current (RF is DC shorted to GND through balun) .....	50mA	Soldering Temperature (reflow) .....	+260°C
Continuous Power Dissipation (Note 1) .....	6.75W		

**Note 1:** Based on junction temperature  $T_J = T_C + (\theta_{JC} \times V_{CC} \times I_{CC})$ . This formula can be used when the temperature of the exposed pad is known while the device is soldered down to PCB. See the Application Information section for details. The junction temperature must not exceed +150°C.

**Note 2:** T<sub>C</sub> is the temperature on the exposed pad of the package. T<sub>A</sub> is the ambient temperature of the device and PCB.

### PACKAGE THERMAL CHARACTERISTICS

Junction-to-Ambient Thermal Resistance (θ <sub>JA</sub> ) (Notes 3, 4) .....	38°C/W	Junction-to-Case Thermal Resistance (θ <sub>JC</sub> ) (Notes 1, 4) .....	7.4°C/W
Junction-to-Board Thermal Resistance (θ <sub>JB</sub> ) .....	12.2°C/W		

**Note 3:** Junction temperature  $T_J = T_A + (\theta_{JA} \times V_{CC} \times I_{CC})$ . This formula can be used when the ambient temperature of the PCB is known. The junction temperature must not exceed +150°C.

**Note 4:** Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to [www.maximintegrated.com/thermal-tutorial](http://www.maximintegrated.com/thermal-tutorial).

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

### DC ELECTRICAL CHARACTERISTICS

(Using the *Typical Application Circuit*, no input RF or LO signals applied, V<sub>CC</sub> = 4.75V to 5.25V, T<sub>C</sub> = -40°C to +85°C. Typical values are at V<sub>CC</sub> = 5.0V, T<sub>C</sub> = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V <sub>CC</sub>		4.75	5	5.25	V
Supply Current	I <sub>CC</sub>	Total supply current (see Table 1 for lower current settings)		400	440	mA
		V <sub>CC</sub> (pin 16)		80		
		V <sub>CC</sub> (pin 30)		80		
		IFM+/IFM- (total of both)		105		
		IFD+/IFD- (total of both)		105		
LOSEL Input High Voltage	V <sub>IH</sub>		2			V
LOSEL Input Low Voltage	V <sub>IL</sub>				0.8	V
LOSEL Input Current	I <sub>IH</sub> and I <sub>IL</sub>		-10		+10	µA

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### AC ELECTRICAL CHARACTERISTICS

(Using the *Typical Application Circuit*,  $V_{CC} = 4.75V$  to  $5.25V$ , RF and LO ports are driven from  $50\Omega$  sources,  $P_{LO} = -3dBm$  to  $+3dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} = 820MHz$  to  $920MHz$ ,  $f_{LO} = 670MHz$  to  $865MHz$ ,  $f_{IF} = 100MHz$ ,  $f_{RF} > f_{LO}$ ,  $T_C = -40^\circ C$  to  $+85^\circ C$ . Typical values are at  $V_{CC} = 5.0V$ ,  $P_{RF} = -5dBm$ ,  $P_{LO} = 0dBm$ ,  $f_{RF} = 870MHz$ ,  $f_{LO} = 770MHz$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.) (Note 5)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
RF Frequency	$f_{RF}$	(Note 6)		700		1000	MHz
LO Frequency	$f_{LO}$	(Note 6)		570		865	MHz
IF Frequency	$f_{IF}$	IF matching components affect the IF frequency range (Note 6)		50		250	MHz
LO Drive	$P_{LO}$	(Note 7)		-3		+3	dBm
Conversion Gain	$G_C$	(Note 8)		4.5	6	7.5	dB
		$T_C = +100^\circ C$			5.4		
Gain Variation over Temperature					-0.012		dB/ $^\circ C$
Conversion Gain Flatness		Flatness over any one of three frequency bands: $f_{RF} = 824MHz$ to $849MHz$ $f_{RF} = 869MHz$ to $894MHz$ $f_{RF} = 880MHz$ to $915MHz$			$\pm 0.1$		dB
Noise Figure, Single Sideband	NF	$f_{IF} = 190MHz$ , no blockers present (Note 7)			10.5	13	dB
Noise Figure under Blocking Condition		+11dBm blocker tone applied to RF port at 961MHz, $f_{RF} = 860MHz$ , $f_{LO} = 670MHz$ , $f_{IFDESIREDD} = 190MHz$ , $f_{BLOCKER} = 291MHz$ (Notes 7, 9)			21	26	dB
Input Compression Point	$P_{1dB}$				16.2		dBm
Output Compression Point	$OP_{1dB}$			18.5	21.2		dBm
Small-Signal Compression under Blocking Conditions		$P_{RF} = -5dBm$ , $f_{RF} = 870MHz$ , $f_{BLOCKER} = 871MHz$	$P_{BLOCKER} = +8dBm$		0.1		dB
			$P_{BLOCKER} = +11dBm$		0.25		
Third-Order Input Intercept Point	IIP3	$f_{RF1} - f_{RF2} = 1MHz$ , $f_{IF} = 100MHz$ , $P_{RF} = -5dBm/$ tone			28.5		dBm
				$T_C = +100^\circ C$	28.8		
Third-Order Input Intercept Point Variation over Temperature					-0.01		dB/ $^\circ C$
Third-Order Output Intercept Point	OIP3	$P_{RF} = -5dBm/$ tone, $f_{IF} = 100MHz$ , $f_{RF1} - f_{RF2} = 1MHz$ (Note 7)		32.0	34.5		dBm
2RF-2LO Spur	2 x 2	$f_{RF} = 870MHz$ , $f_{LO} = 770MHz$ , $f_{SPUR} = 820MHz$	$P_{RF} = -10dBm$ (Note 7)		63	77	dBc
			$P_{RF} = -10dBm$ , $T_C = +100^\circ C$			78	
			$P_{RF} = -5dBm$ (Note 7)		58	72	
			$P_{RF} = -5dBm$ , $T_C = +100^\circ C$			73	
3RF-3LO Spur	3 x 3	$f_{RF} = 870MHz$ , $f_{LO} = 770MHz$ , $f_{SPUR} = 803.3MHz$	$P_{RF} = -10dBm$ (Note 7)		70	85	dBc
			$P_{RF} = -10dBm$ , $T_C = +100^\circ C$			87.3	
			$P_{RF} = -5dBm$ (Note 7)		60	75	
			$P_{RF} = -5dBm$ , $T_C = +100^\circ C$			77.3	

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### AC ELECTRICAL CHARACTERISTICS (continued)

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
LO1-to-LO2 Port Isolation		$P_{LO1} = +3dBm$ , $P_{LO2} = +3dBm$ , $f_{LO1}-f_{LO2} = 1MHz$ , $P_{RF} = -5dBm$ , $f_{IF} = 100MHz$ (Notes 7, 10)	39	43		dB
Maximum LO Leakage at RF Port				-40	-30	dBm
Maximum 2LO Leakage at RF Port				-45	-20	dBm
Maximum LO Leakage at IF Port				-30	-20	dBm
		$T_C = +100^\circ C$		-30.3		
Minimum RF-to-IF Isolation			30	45		dB
		$T_C = +100^\circ C$		49.5		
Minimum Channel-to-Channel Isolation		$P_{RF} = -10dBm$ , RFMAIN (RFDIV) power measured at IFDIV (IFMAIN), relative to IFMAIN (IFDIV), all unused ports terminated to $50\Omega$		40	47	dB
			$T_C = +100^\circ C$		47.5	
LO Switching Time		50% of LOSEL to IF settled within 2 degrees (Note 7)		0.05	1	$\mu s$
RF Input Impedance				50		$\Omega$
LO Input Impedance				50		$\Omega$
IF Output Impedance		Differential		200		$\Omega$
RF Input Return Loss		LO on and IF terminated		24		dB
LO Input Return Loss		LO port selected		35		dB
		LO port unselected		36		
IF Return Loss		RF terminated in $50\Omega$		20		dB

**Note 5:** All limits reflect losses of external components. Output measurements taken at IF outputs of the *Typical Application Circuit*.

**Note 6:** Performance is guaranteed for  $f_{RF} = 820MHz$  to  $920MHz$ ,  $f_{LO} = 670MHz$  to  $865MHz$ , and  $f_{IF} = 100MHz$ . Operation outside this range is possible, but with degraded performance of some parameters. See the *Typical Operating Characteristics*.

**Note 7:** Guaranteed by design and characterization.

**Note 8:** Performance at  $T_C = -40^\circ C$  is guaranteed by design.

**Note 9:** Measured with external LO source noise filtered so the noise floor is  $-174dBm/Hz$ . This specification reflects the effects of all SNR degradations in the mixer including the LO noise, as defined in Maxim Application Note 2021.

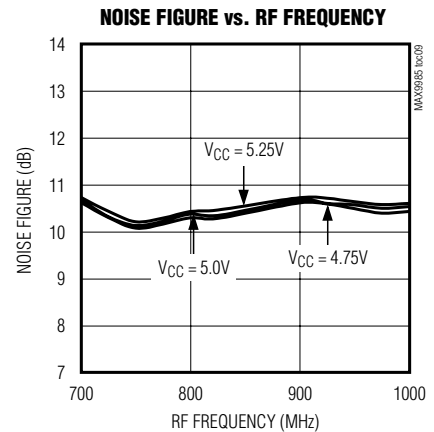
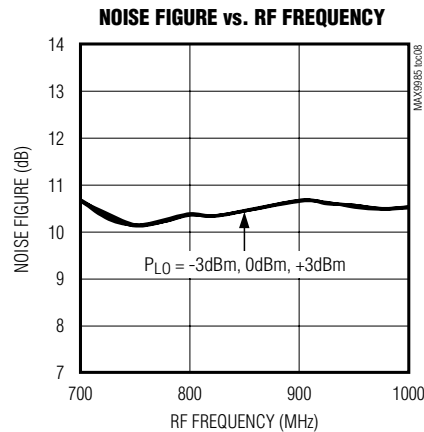
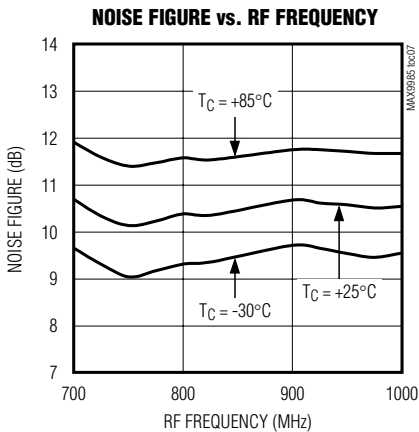
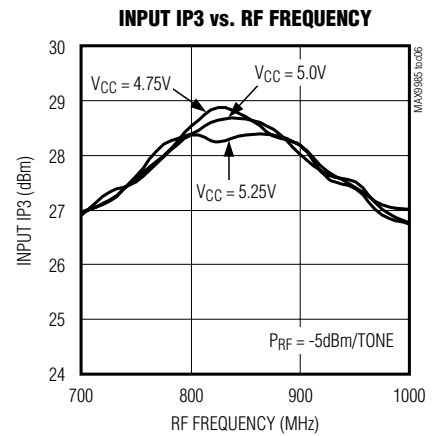
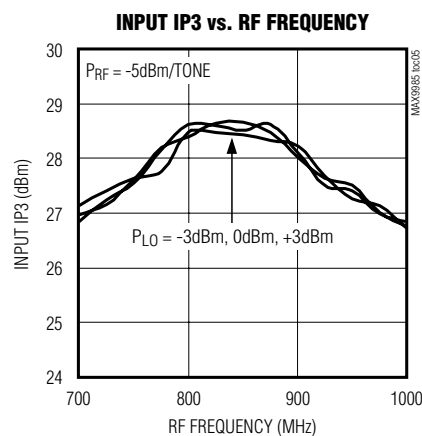
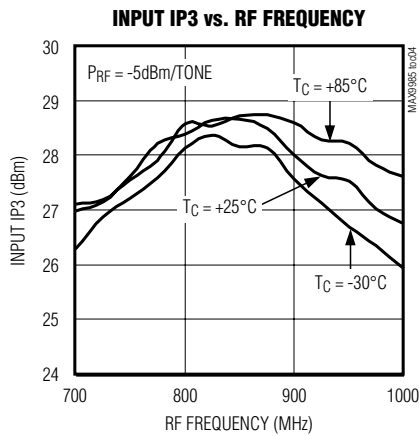
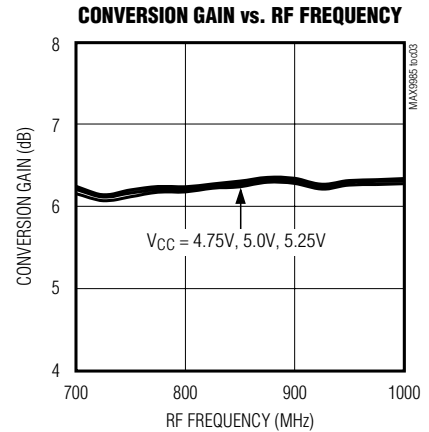
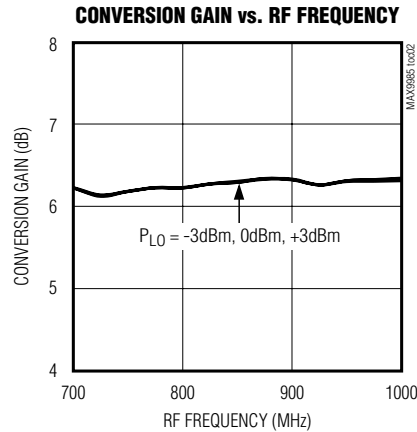
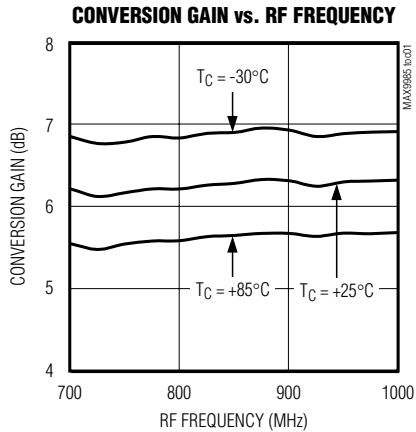
**Note 10:** Measured at IF port at IF frequency. LOSEL may be in any logic state.

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### Typical Operating Characteristics

(Using the *Typical Application Circuit*,  $V_{CC} = 5.0V$ ,  $P_{LO} = 0dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} > f_{LO}$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.)

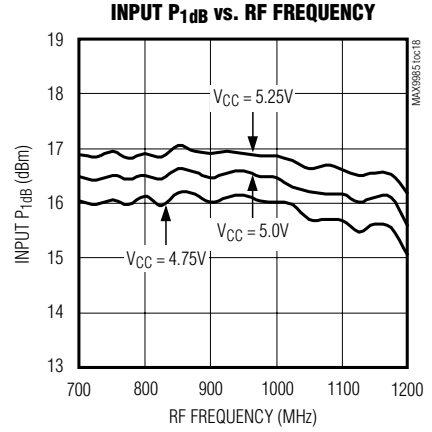
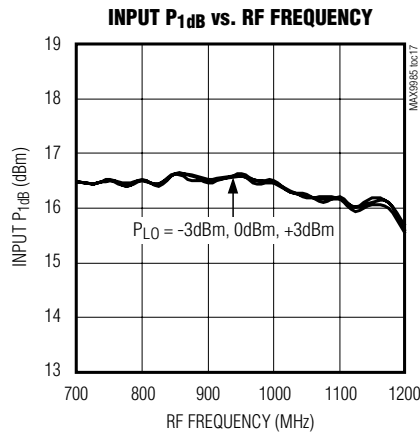
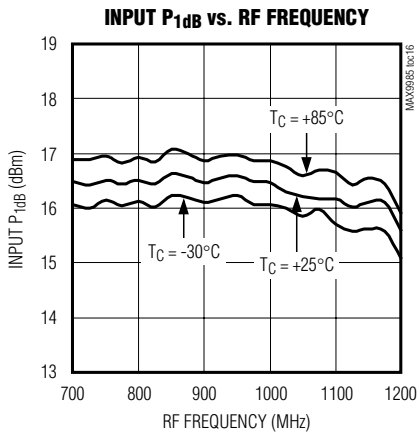
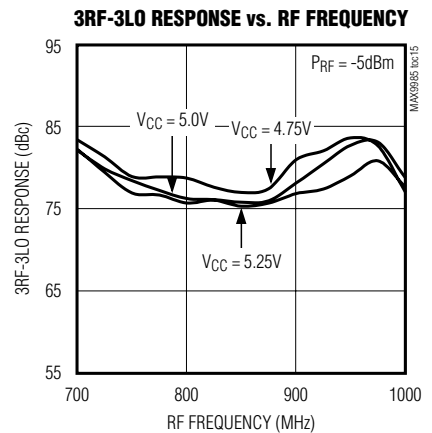
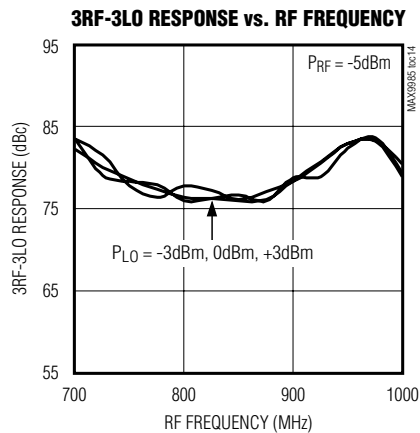
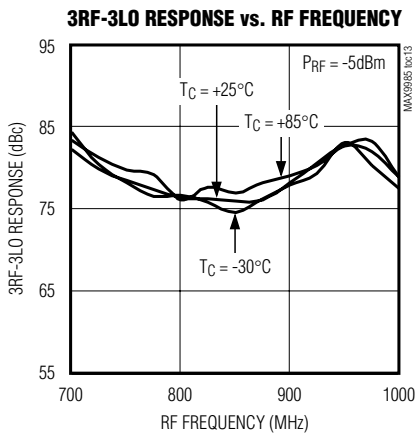
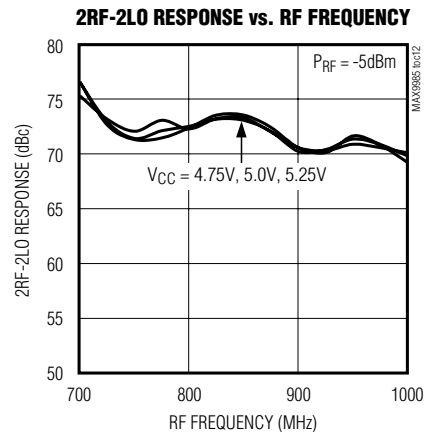
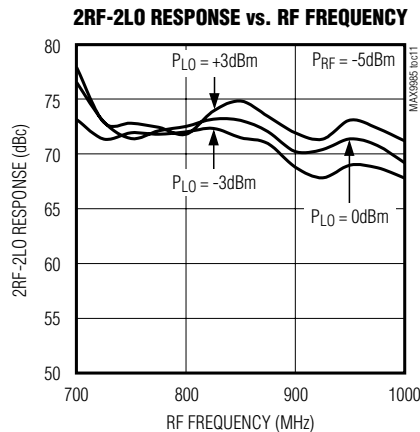
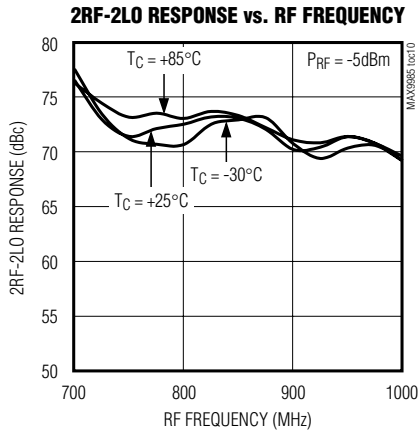


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## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Typical Operating Characteristics (continued)

(Using the Typical Application Circuit,  $V_{CC} = 5.0V$ ,  $P_{LO} = 0dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} > f_{LO}$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.)



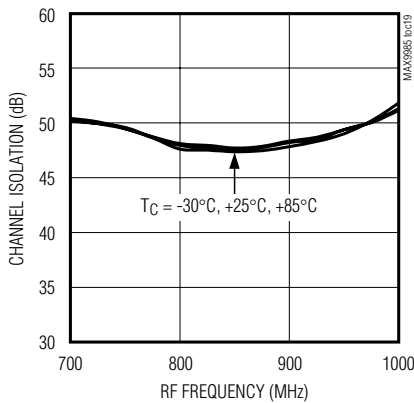
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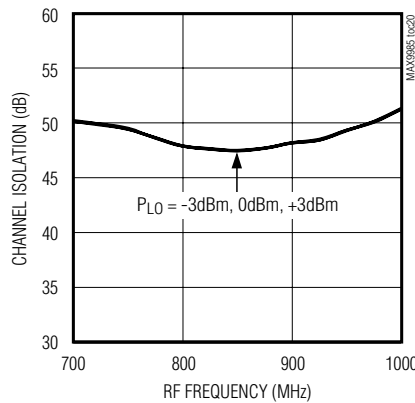
### Typical Operating Characteristics (continued)

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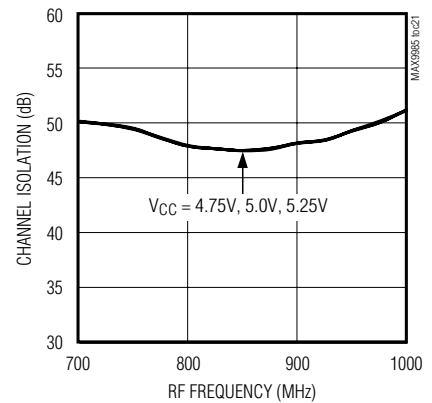
CHANNEL ISOLATION vs. RF FREQUENCY



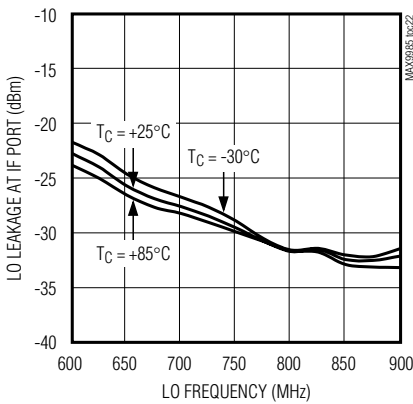
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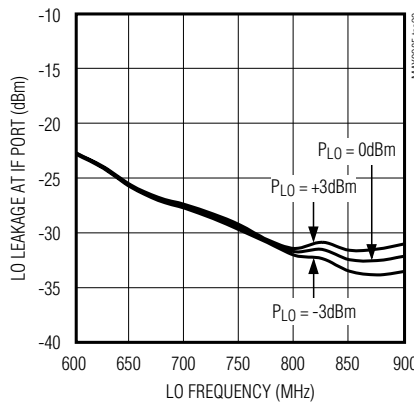
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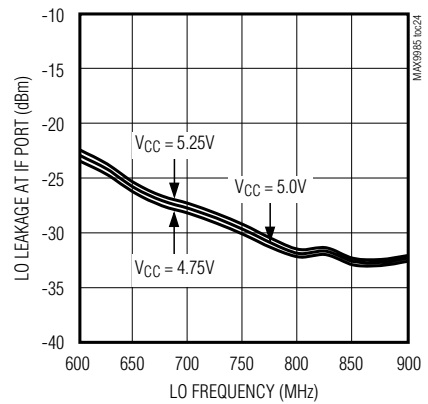
LO LEAKAGE AT IF PORT vs. LO FREQUENCY



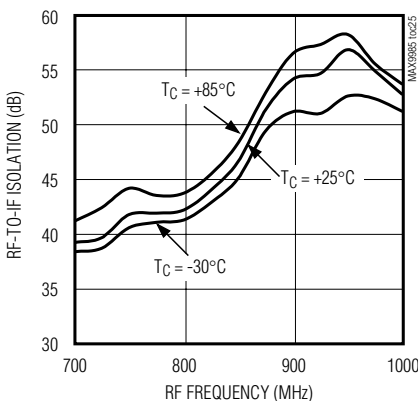
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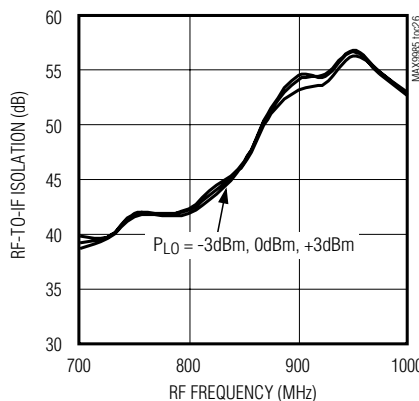
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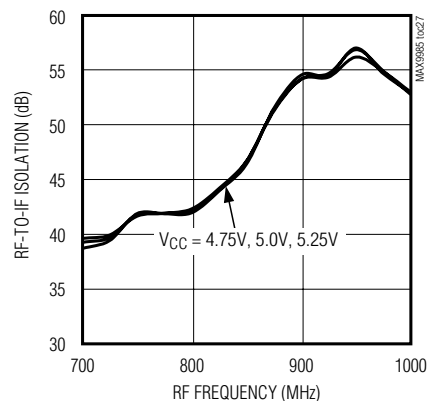
RF-TO-IF ISOLATION vs. RF FREQUENCY



RF-TO-IF ISOLATION vs. RF FREQUENCY



RF-TO-IF ISOLATION vs. RF FREQUENCY



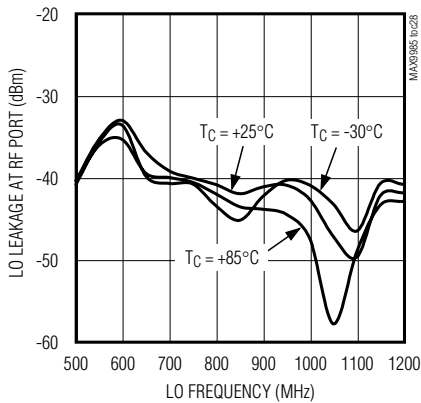
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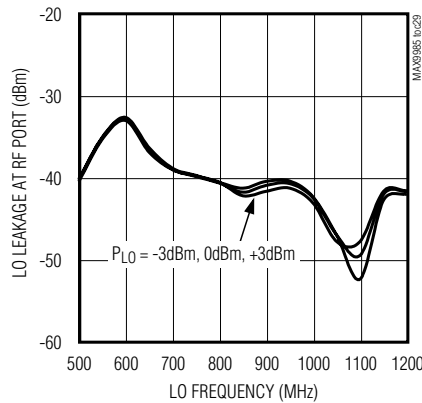
### Typical Operating Characteristics (continued)

(Using the *Typical Application Circuit*,  $V_{CC} = 5.0V$ ,  $P_{LO} = 0dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} > f_{LO}$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.)

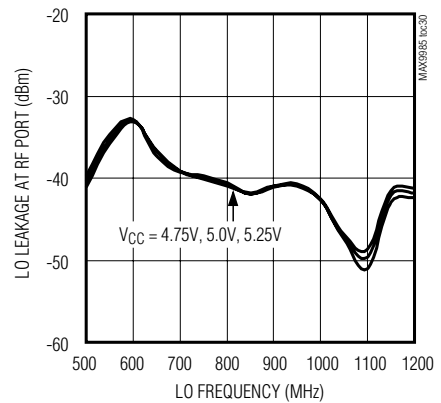
**LO LEAKAGE AT RF PORT vs. LO FREQUENCY**



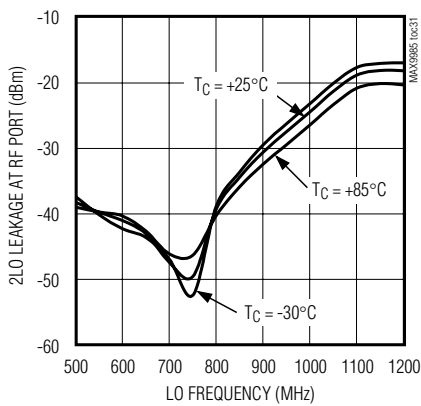
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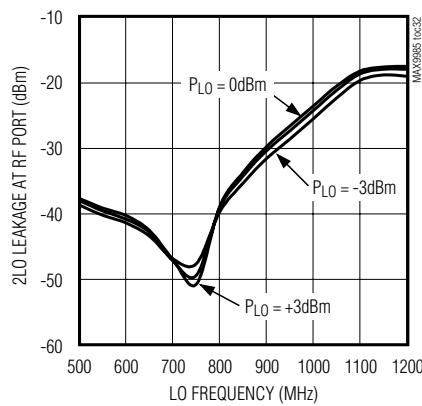
**LO LEAKAGE AT RF PORT vs. LO FREQUENCY**



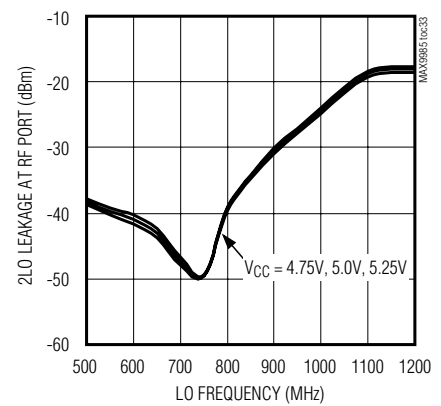
**2LO LEAKAGE AT RF PORT vs. LO FREQUENCY**



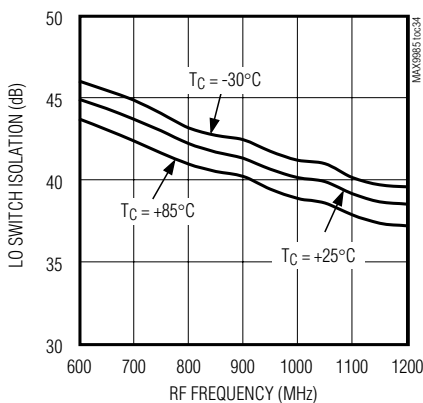
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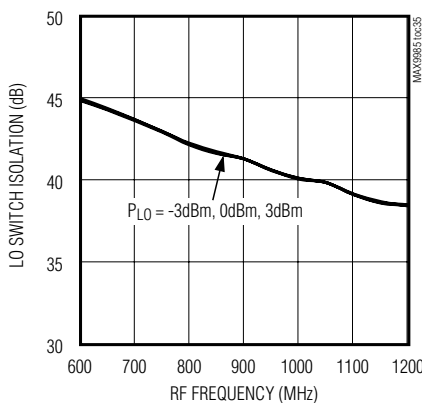
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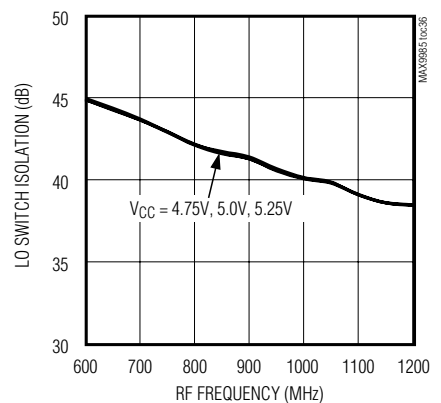
**LO SWITCH ISOLATION vs. RF FREQUENCY**



**LO SWITCH ISOLATION vs. RF FREQUENCY**



**LO SWITCH ISOLATION vs. RF FREQUENCY**

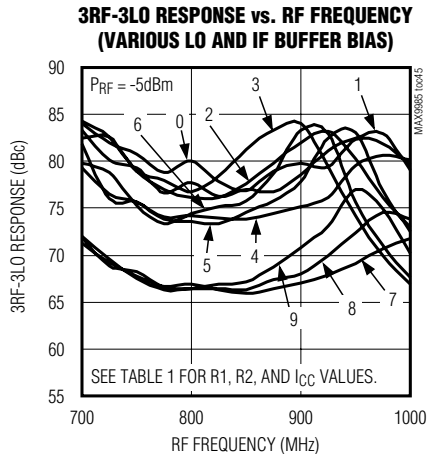
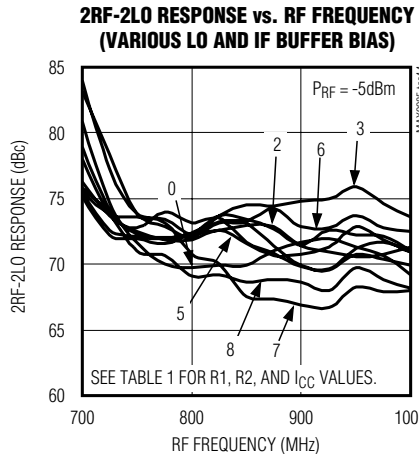
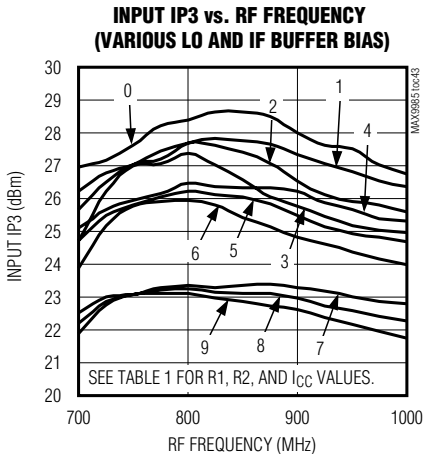
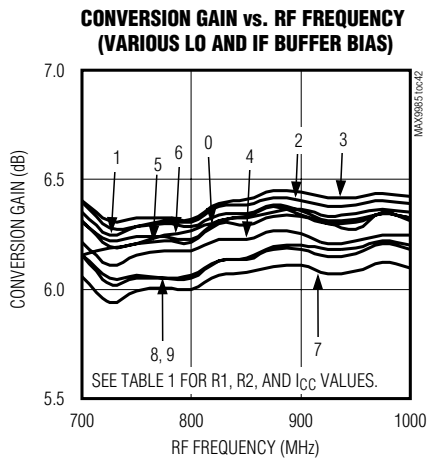
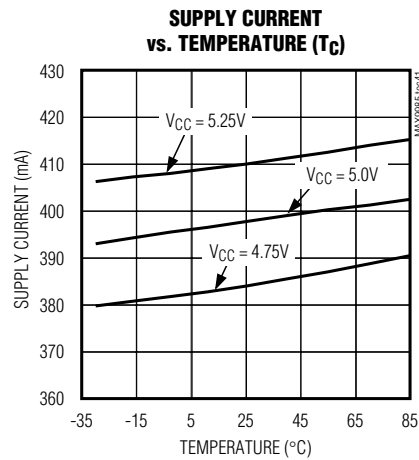
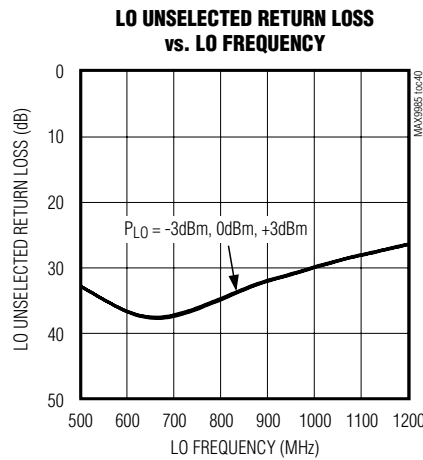
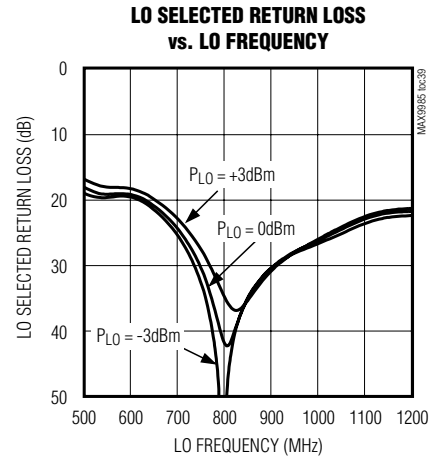
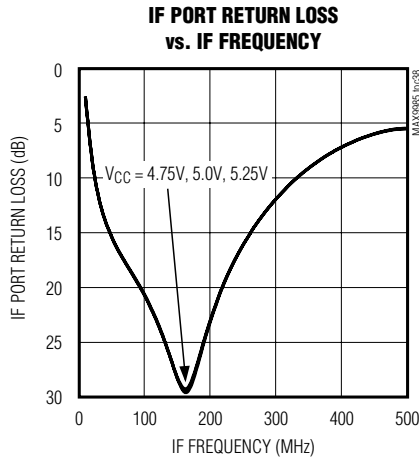
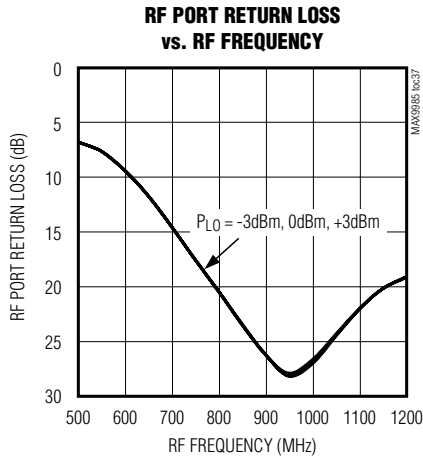


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## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Typical Operating Characteristics (continued)

(Using the Typical Application Circuit,  $V_{CC} = 5.0V$ ,  $P_{LO} = 0dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} > f_{LO}$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.)



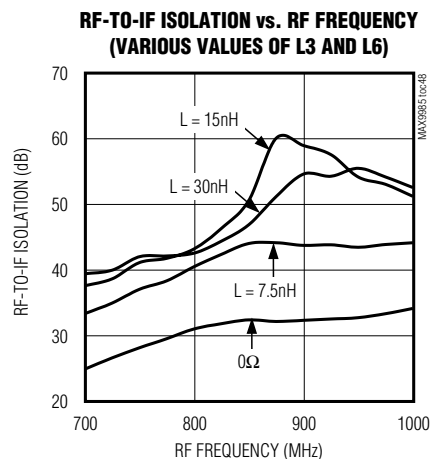
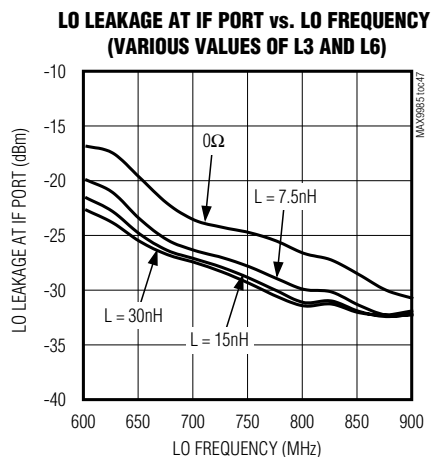
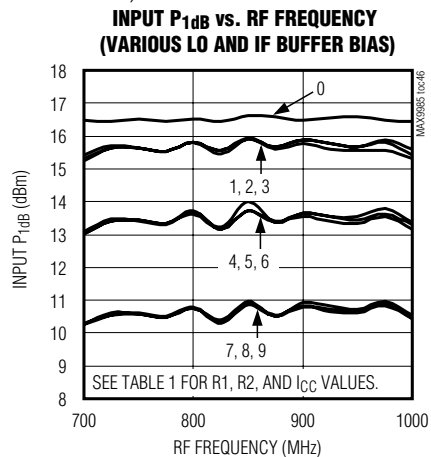


# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Typical Operating Characteristics (continued)

(Using the *Typical Application Circuit*,  $V_{CC} = 5.0V$ ,  $P_{LO} = 0dBm$ ,  $P_{RF} = -5dBm$ ,  $f_{RF} > f_{LO}$ ,  $f_{IF} = 100MHz$ ,  $T_C = +25^\circ C$ , unless otherwise noted.)



**Table 1. DC Current vs. Bias Resistor Settings**

BIAS CONDITION	DC CURRENT (mA)	R1 AND R4 VALUES ( $\Omega$ )	R2 AND R5 VALUES ( $\Omega$ )
0	397.8	1070	1100
1	345.0	1400	1100
2	316.5	1400	1620
3	297.5	1400	2210
4	301.2	1910	1100
5	271.7	1910	1620
6	252.2	1910	2210
7	260.1	2800	1100
8	230.5	2800	1620
9	211.5	2800	2210

# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Pin Description

PIN	NAME	FUNCTION
1	RFMAIN	Main Channel RF input. Internally matched to 50Ω. Requires an input DC-blocking capacitor.
2	TAPMAIN	Main Channel Balun Center Tap. Bypass to GND with capacitors close to the pin.
3, 5, 7, 12, 20, 22, 24, 25, 26, 34	GND	Ground
4, 6, 10, 16, 21, 30, 36	V <sub>CC</sub>	Power Supply. Connect bypass capacitors as close to the pin as possible (see the <i>Typical Application Circuit</i> ).
8	TAPDIV	Diversity Channel Balun Center Tap. Bypass to GND with capacitors close to the pin.
9	RFDIV	Diversity Channel RF Input. Internally matched to 50Ω. Requires an input DC-blocking capacitor.
11	IFDBIAS	IF Diversity Amplifier Bias Control. Connect a 1.07kΩ resistor from this pin to ground to set the bias current for the diversity IF amplifier (see the <i>Typical Operating Characteristics</i> for typical performance versus resistor value).
13, 14	IFD+, IFD-	Diversity Mixer Differential IF Output. Connect pullup inductors from each of these pins to V <sub>CC</sub> (see the <i>Typical Application Circuit</i> ).
15	LEXTD	Connect a 30nH inductor from this pin to ground to increase the RF-to-IF and LO-to-IF isolation. Connect this pin to ground if isolations can be degraded (see the <i>Typical Operating Characteristics</i> for typical degradation).
17	LODBIAS	LO Diversity Amplifier Bias Control. Connect a 1.1kΩ resistor from this pin to ground to set the bias current for the diversity LO amplifier (see the <i>Typical Operating Characteristics</i> for typical performance versus resistor value).
18, 28	N.C.	No Connection. Not internally connected.
19	LO1	Local Oscillator 1 Input. This input is internally matched to 50Ω. Requires an input DC-blocking capacitor.
23	LOSEL	Local Oscillator Select. Set this pin to high to select LO1. Set low to select LO2.
27	LO2	Local Oscillator 2 Input. This input is internally matched to 50Ω. Requires an input DC-blocking capacitor.
29	LOMBIAS	LO Main Amplifier Bias Control. Connect a 1.1kΩ resistor from this pin to ground to set the bias current for the main LO amplifier (see the <i>Typical Operating Characteristics</i> for typical performance versus resistor value).
31	LEXTM	Connect a 30nH inductor from this pin to ground to increase the RF-IF and LO-IF isolation. Connect this pin to ground if isolations can be degraded (see the <i>Typical Operating Characteristics</i> for typical degradation).
32, 33	IFM-, IFM+	Main Mixer Differential IF Output. Connect pullup inductors from each of these pins to V <sub>CC</sub> (see the <i>Typical Application Circuit</i> ).
35	IFMBIAS	IF Main Amplifier Bias Control. Connect a 1.07kΩ resistor from this pin to ground to set the bias current for the main IF amplifier (see the <i>Typical Operating Characteristics</i> for typical performance vs. resistor value).
—	EP	Exposed Paddle. Solder the exposed paddle to the ground plane using multiple vias. This paddle affects RF performance and provides heat dissipation.

# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Detailed Description

The MAX9985 is a dual-channel downconverter designed to provide 6dB of conversion gain, +28.5dBm input IP3, and +16.2dBm 1dB input compression point, with a 10.5dB NF.

In addition to its high-linearity performance, the MAX9985 achieves a high level of component integration. The device integrates two double-balanced active mixers for two-channel downconversion. Both the main and diversity channels include a balun and matching circuitry to allow 50Ω single-ended interfaces to the RF ports and the two LO ports. An integrated single-pole, double-throw (SPDT) switch provides 50ns switching time between the two LO inputs with 43dB of LO-to-LO isolation and a -40dBm of LO leakage at the RF port. Furthermore, the integrated LO buffers provide a high drive level to each mixer core, reducing the LO drive required at the MAX9985's inputs to a -3dBm to +3dBm range. The IF ports for both channels incorporate differential outputs for downconversion, which is ideal for providing enhanced IIP2 performance.

Dual-channel downconversion makes the MAX9985 ideal for diversity receiver applications. In addition, specifications are guaranteed over broad frequency ranges to allow for use in GSM 850/950, 2G/2.5G EDGE, WCDMA, cdma2000, and iDEN base stations. The MAX9985 is specified to operate over a 700MHz to 1000MHz RF input range, a 570MHz to 865MHz LO range, and a 50MHz to 250MHz IF range. The external IF components set the lower frequency range (see the *Typical Operating Characteristics* for details).

### RF Port and Balun

The RF input ports to both the main and diversity channels are internally matched to 50Ω, requiring no external matching components. A DC-blocking capacitor is required as the input is internally DC-shortened to ground through the on-chip balun. The RF port return loss is typically 15dB over the entire 700MHz to 1000MHz RF frequency range.

### LO Inputs, Buffer, and Balun

The MAX9985 is optimized for a 570MHz to 865MHz LO frequency range. As an added feature, the MAX9985 includes an internal LO SPDT switch for use in frequency-hopping applications. The switch selects one of the two single-ended LO ports, allowing the external oscillator to settle on a particular frequency before it is switched in. LO switching time is typically less than 50ns, which is more than adequate for typical GSM applications. If frequency hopping is not employed, simply set the switch to either of the LO inputs. The switch is controlled by a digital input

(LOSEL), where logic-high selects LO1 and logic-low selects LO2. LO1 and LO2 inputs are internally matched to 50Ω, requiring only an 82pF DC-blocking capacitor. To avoid damage to the part, voltage **MUST** be applied to VCC before digital logic is applied to LOSEL. Alternatively, a 1kΩ resistor can be placed in series at the LOSEL to limit the input current in applications where LOSEL is applied before VCC.

The main and diversity channels incorporate a two-stage LO buffer that allows for a wide-input power range for the LO drive. All guaranteed specifications are for an LO signal power from -3dBm to +3dBm. The on-chip low-loss baluns, along with LO buffers, drive the double-balanced mixers. All interfacing and matching components from the LO inputs to the IF outputs are integrated on-chip.

### High-Linearity Mixer

The core of the MAX9985 dual-channel downconverter consists of two double-balanced, high-performance passive mixers. Exceptional linearity is provided by the large LO swing from the on-chip LO buffers. When combined with the integrated IF amplifiers, the cascaded IIP3, 2RF-2LO rejection, and NF performance are typically +28.5dBm, 77dBc, and 10.5dB, respectively.

### Differential IF

The MAX9985 has a 50MHz to 250MHz IF frequency range, where the low-end frequency depends on the frequency response of the external IF components. Note that these differential ports are ideal for providing enhanced IIP2 performance. Single-ended IF applications require a 4:1 (impedance ratio) balun to transform the 200Ω differential IF impedance to a 50Ω single-ended system. After the balun, the IF return loss is better than 20dB. The user can use a differential IF amplifier on the mixer IF ports, but a DC block is required on both IFD+/IFD- and IFM+/IFM- ports to keep external DC from entering the IF ports of the mixer.

## Applications Information

### Input and Output Matching

The RF and LO inputs are internally matched to 50Ω. No matching components are required. Return loss at the RF port is typically 15dB over the entire input range and return loss at the LO ports are typically 25dB. RF and LO inputs require only DC-blocking capacitors for interfacing.

The IF output impedance is 200Ω (differential). For evaluation, an external low-loss 4:1 (impedance ratio) balun transforms this impedance to a 50Ω single-ended output (see the *Typical Application Circuit*).

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### LO Buffer Bias Resistors

Bias currents for the two on-chip LO buffers is optimized by fine-tuning the off-chip resistors on LODBIAS (pin 17) and LOMBIAS (pin 29). The current in the buffer amplifiers is reduced by increasing the value of these resistors, but performance may degrade. See the *Typical Operating Characteristics* for key performance parameters versus this resistor value. Doubling the value of these resistors reduces the total chip current by approximately 50mA (see Table 1).

### IF Amplifier Bias Resistors

Bias currents for the two on-chip IF amplifiers are optimized by fine-tuning the off-chip resistors on IFDBIAS (pin 11) and IFMBIAS (pin 35). The current in the IF amplifiers is decreased by raising the value of these resistors, but performance may degrade. See the *Typical Operating Characteristics* for key performance parameters versus this resistor value. Doubling the value of this resistor reduces the current in each IF amplifier from 100mA to approximately 50mA (see Table 1).

### LEXT Inductor

Short LEXT\_ to ground using a 0Ω resistor. For applications requiring improved RF-to-IF and LO-to-IF isolation, LEXT\_ can be used by connecting a low-ESR inductor from LEXT\_ to GND. See the *Typical Operating Characteristics* on RF-to-IF port isolation and LO-to-IF port leakage for various inductor values. The load impedance presented to the mixer must be such that any capacitance from both IF- and IF+ to ground do not exceed several picofarads to ensure stable operating conditions.

Approximately 100mA flows through LEXT\_, so it is important to use a low-DCR wire-wound inductor.

### Layout Considerations

A properly designed PCB is an essential part of any RF/microwave circuit. Keep RF signal lines as short as possible to reduce losses, radiation, and inductance. For the best performance, route the ground pin traces directly to the exposed paddle under the package. The PCB exposed paddle **MUST** be connected to the ground plane of the PCB. It is suggested that multiple vias be used to connect this paddle to the lower-level ground planes. This method provides a good RF/thermal-conduction path for the device. Solder the exposed paddle on the bottom of the device package to the PCB. Refer to the *MAX9985 Evaluation Kit* as a reference for board layout. Gerber files are available upon request at [www.maxim-ic.com](http://www.maxim-ic.com).

### Power-Supply Bypassing

Proper voltage-supply bypassing is essential for high-frequency circuit stability. Bypass each VCC pin and TAPMAIN/TAPDIV with the capacitors shown in the *Typical Application Circuit* (see Table 2 for component values). Place the TAPMAIN/TAPDIV bypass capacitor to ground within 100 mils of the pin.

Table 2. Component Values

COMPONENT	VALUE	DESCRIPTION
C1, C2, C7, C8	39pF	Microwave capacitors (0402)
C3, C6	0.033μF	Microwave capacitors (0603)
C4, C5	—	Not used
C9, C13, C15, C17, C18	0.01μF	Microwave capacitors (0402)
C10, C11, C12, C19, C20, C21	150pF	Microwave capacitors (0603)
C14, C16	82pF	Microwave capacitors (0402)
L1, L2, L4, L5	560nH	Wire-wound high-Q inductors (0805)
L3, L6	30nH	Wire-wound high-Q inductors (0603)
R1, R4	1.07kΩ	±1% resistors (0402)
R2, R5	1.1kΩ	±1% resistors (0402)
R3, R6	0Ω	Resistors (1206)
T1, T2	4:1	Transformers (200:50) Mini-Circuits TC4-1W-7A
U1	—	MAX9985 IC

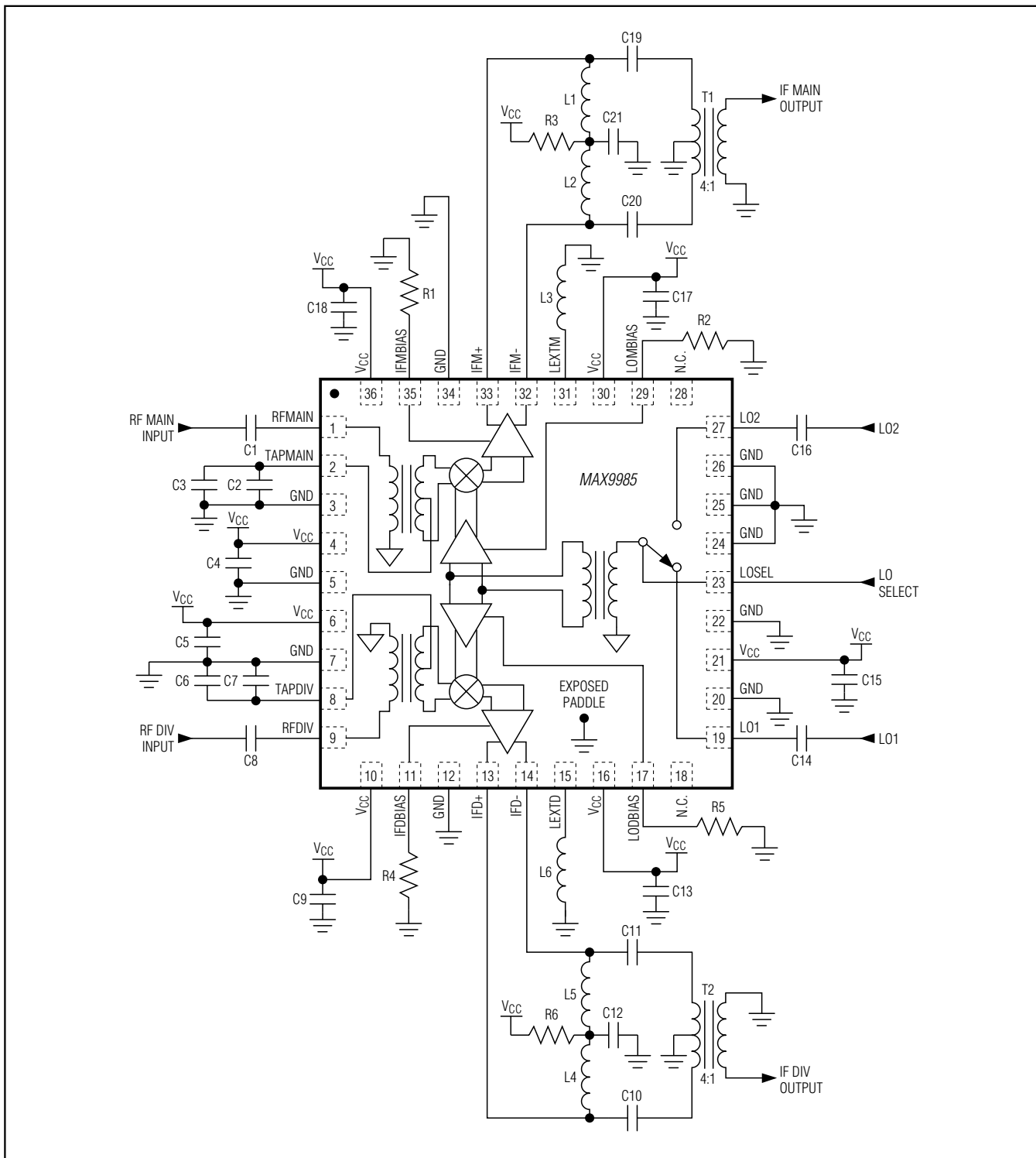
### Exposed Paddle RF/Thermal Considerations

The exposed paddle (EP) of the MAX9985's 36-pin thin QFN-EP package provides a low thermal-resistance path to the die. It is important that the PCB on which the MAX9985 is mounted be designed to conduct heat from the EP. In addition, provide the EP with a low-inductance path to electrical ground. The EP **MUST** be soldered to a ground plane on the PCB, either directly or through an array of plated via holes.

# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

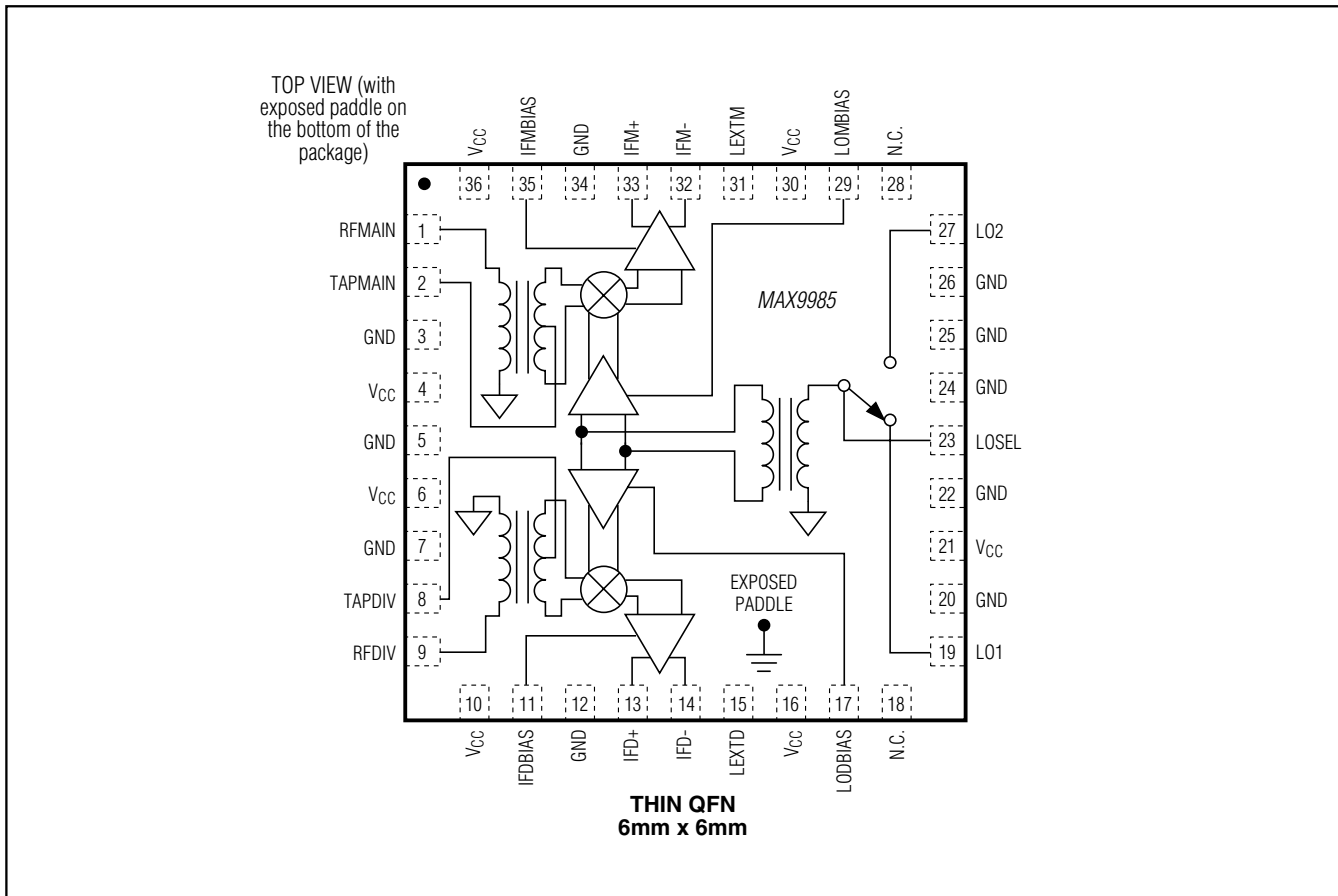
### Typical Application Circuit



# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Pin Configuration/Functional Diagram



### Chip Information

PROCESS: SiGe BiCMOS

### Lead-Free/RoHS Considerations

<http://www.maximintegrated.com/emmi/faq.cfm>

### Reliability Information:

<http://www.maximintegrated.com/reliability/product/MAX9985.pdf>

### Package Information

For the latest package outline information and land patterns (footprints), go to [www.maximintegrated.com/packages](http://www.maximintegrated.com/packages). Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

# MAX9985

## Dual, SiGe, High-Linearity, 700MHz to 1000MHz Downconversion Mixer with LO Buffer/Switch

### Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	12/06	Initial release	—
1	1/07	Updated <i>Electrical Characteristics</i> table	2, 3
2	12/12	Updated <i>Electrical Characteristics</i> table, <i>Absolute Maximum Ratings</i> , and <i>Ordering Information</i>	1–4, 15



Maxim Integrated cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim Integrated product. No circuit patent licenses are implied. Maxim Integrated reserves the right to change the circuitry and specifications without notice at any time. The parametric values (min and max limits) shown in the *Electrical Characteristics* table are guaranteed. Other parametric values quoted in this data sheet are provided for guidance.

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